

NTS330P06C



P-Channel Enhancement Mode Trench Power MOSFET

Voltage:	-60 Volts	Current:	-35 Ampers	Package:	TO-220C
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Features

- > NH'S Advanced Trench Technology
- > Low Rds(on) For Low On-State Loss
- > High EAS For High Reliability
- > Excellent Qg*Rds(on) Product(FOM)

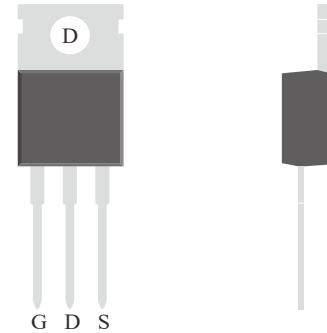
Typical Applications

- > DC-DC Converter
- > Battery Management System(BMS)
- > Printed Circuit Board For Control Circuit
- > Uninterruptible Power Supplies(UPS)

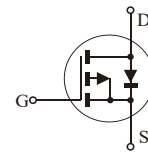
Product Summary

VDS Min.@Tj	-60	V
ID Min.@Ta	-35	A
RDS(ON)(TYP)@-10V	25	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	-60	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 ℃	I _D	-35	A
	Ta= 100 ℃		-32	
Drain Current-Pulse (Note 1)	Tj< 175 ℃	I _{DM}	-140	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25℃	Ta= 25 ℃	P _D	88	W
	Ta= 100 ℃		44	
Derating Factor		D _F	0.59	W/℃
Avalanche Current, Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	-44	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.16	L= 0.5 mH	E _{AS}	484	mJ
	I _{AS} = -44 A, R _G = 10.0 Ω Starting Tj=25 ℃, V _G = -10 V			

Thermal Characteristics (Ta=25℃ Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 175	℃
Storage Temperature Range		T _{STD}	-55 to 175	℃
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25℃	R _{θJA}	62.5	℃/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 75mm x 45mm x 2.5mm Alu. Heat.	R _{θJC}	1.7	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 13).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=-250uA	BV _{DSS}	-60	--	--	V
Bvdss Temperature Coefficient	ID=-250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.06	--	V/℃
Drain-Source Leakage Current	VDS= -60 V,VGS=0V	I _{DSS}	--	--	-1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= -17.5 A,VDS= -5 V	g _{fs}	--	26	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=-250uA	V _{GS(TH)}	-1	-1.8	-2.5	V
Drain-Source On Resistance	ID= -17.5 A,VGS= -10 V	R _{DS(ON)}	--	25	33	mΩ
	ID= -17.5 A,VGS= -4.5 V		--	33	50	
Dynamic Characteristics						
Input Capacitance	VDS= -30 V	C _{iss}	--	3600	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	145	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	130	--	pF
Switching Paramters (Test Circuit & Waveform See Fig.14)						
Turn-On Delay Time	VDS= -30 V	t _{d(on)}	--	15	--	ns
Turn-On Rise Time	VGS= -10.0 V	t _r	--	12	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	95	--	ns
Turn-Off Rise Time		t _f	--	35	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.15)						
Total Gate Charge	VDS= -30 V	Q _g	--	65	--	nC
Gate-Source Charge	VGS= -10.0 V	Q _{gs}	--	10	--	nC
Gate-Drain Charge	ID= -17.5 A	Q _{gd}	--	12	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.17)						
Max. Diode Forward Cuurent		I _S	--	--	-35.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	-140	A
Diode Forward Voltage	ID= -17.5 A,VGS=0V	V _{SD}	--	-0.84	-1.2	V
Reverse Recovery Time	IS= -17.5 A,di/dt= -100 A/us	t _{rr}	--	23	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	21	--	nC
Reverse Recovery Current		I _{RRM}	--	-2.0	--	A

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Typical Characteristics Curves

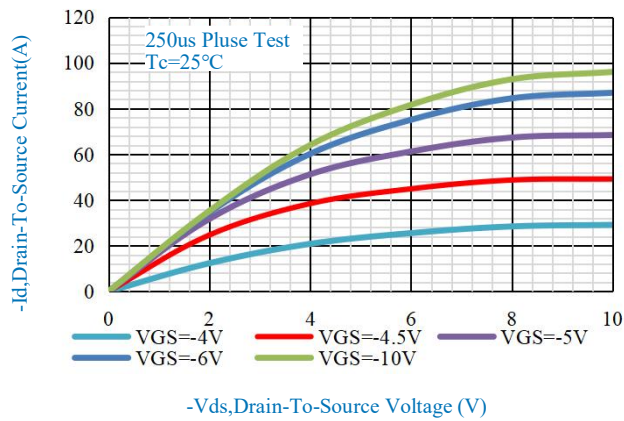


Fig.1-Output Characteristics

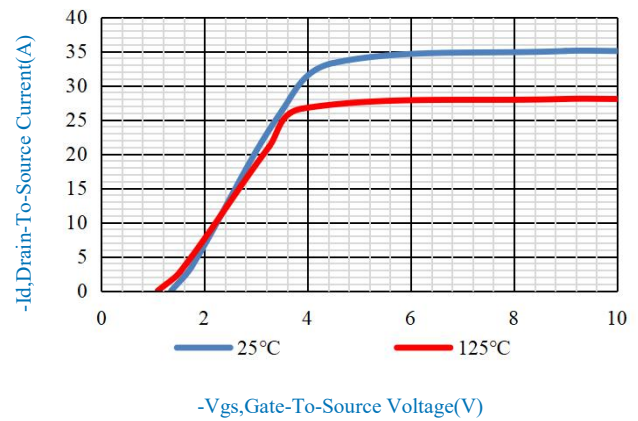


Fig.2-Transfer Characteristics

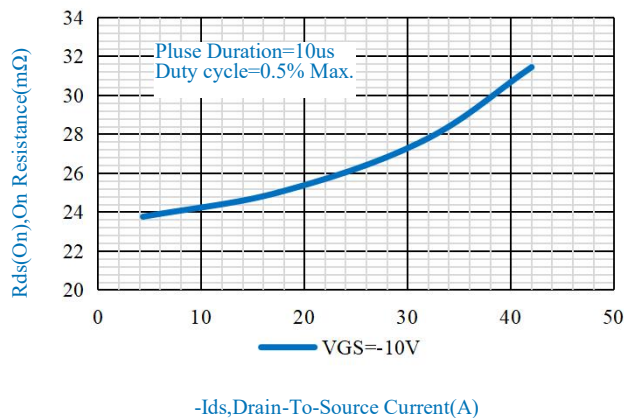


Fig.3-On Resistance Vs. Drain Current

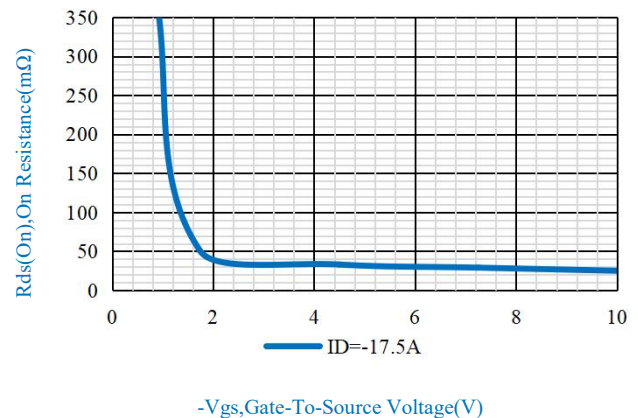


Fig.4-On Resistance Vs. Gate Source Voltage

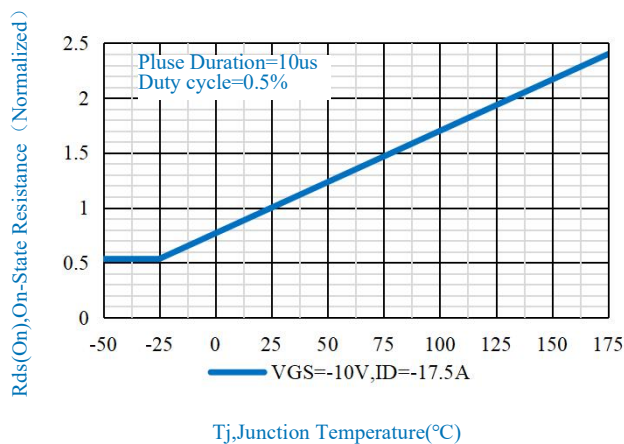


Fig.5-On Resistance Vs. Junction Temperature

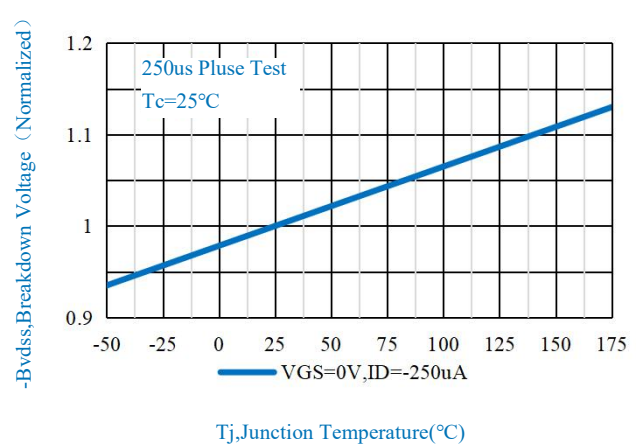


Fig.6-Breakdown Voltage Vs. Junction Temperature

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Typical Characteristics Curves

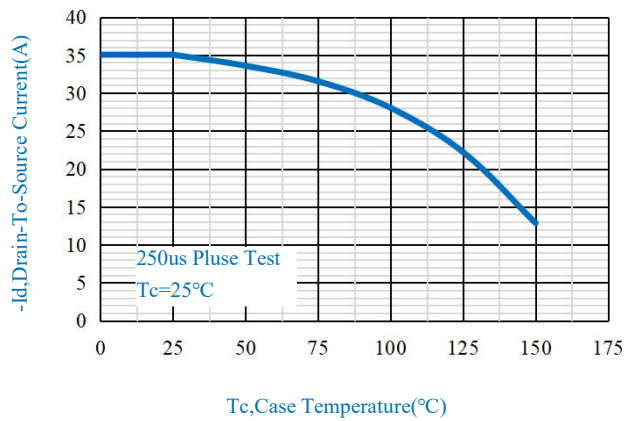


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

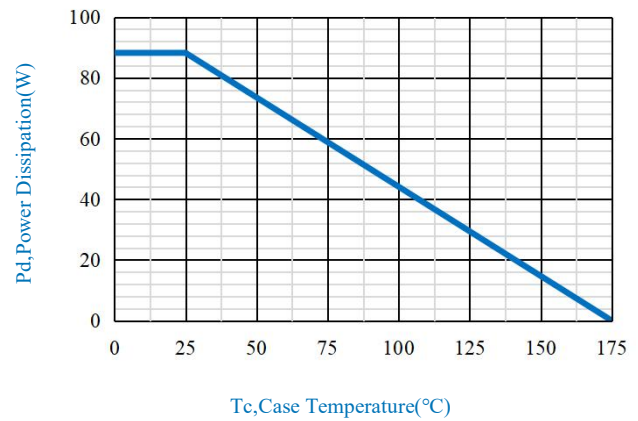


Fig.8-Maximum Power Dissipation Vs. Case Temperature

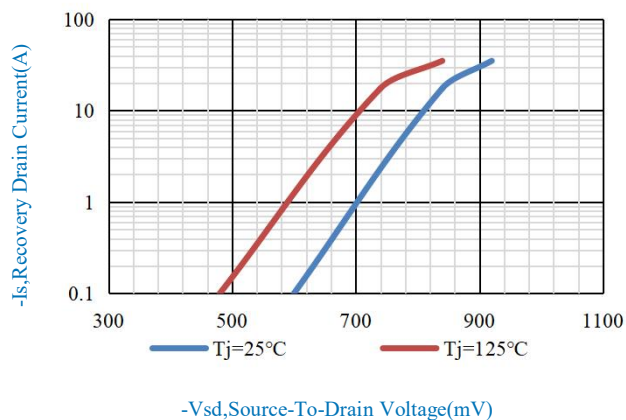


Fig.9-Source-To-Drain Diode Forward Voltage

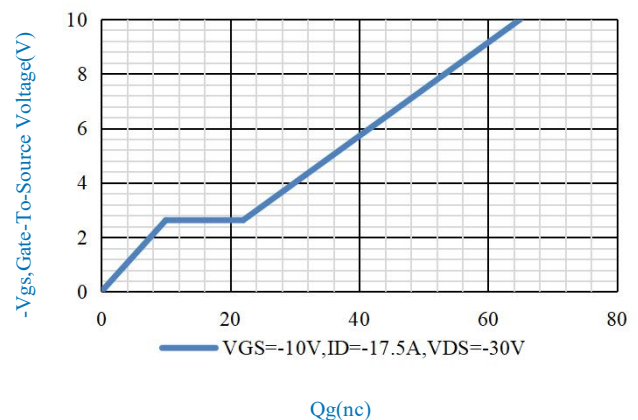


Fig.10-Gate Charge Waveform

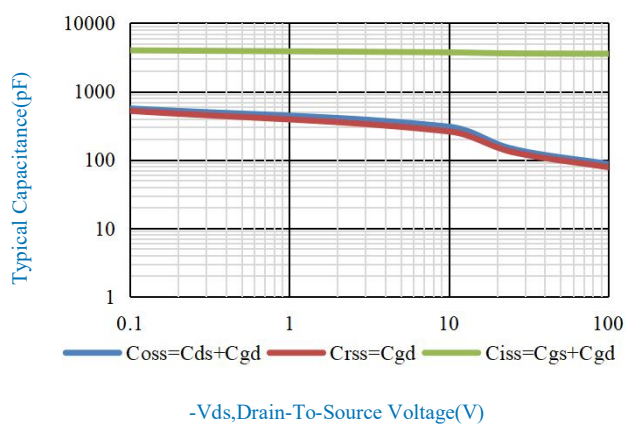


Fig.11-Typical Capacitance Vs. Drain-To-Source Voltage

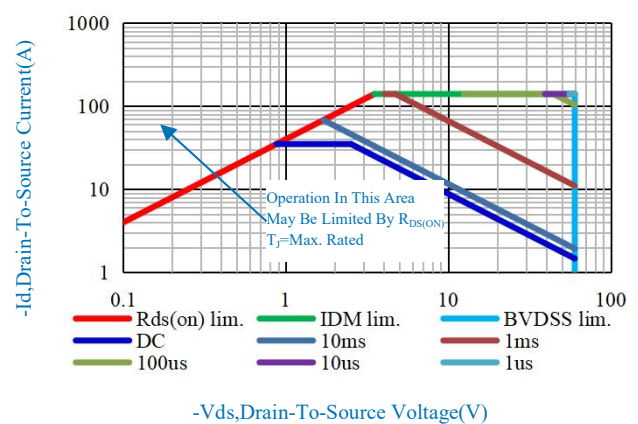


Fig.12-Maximum Safe Operating Area(SOA)

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Typical Characteristics Curves

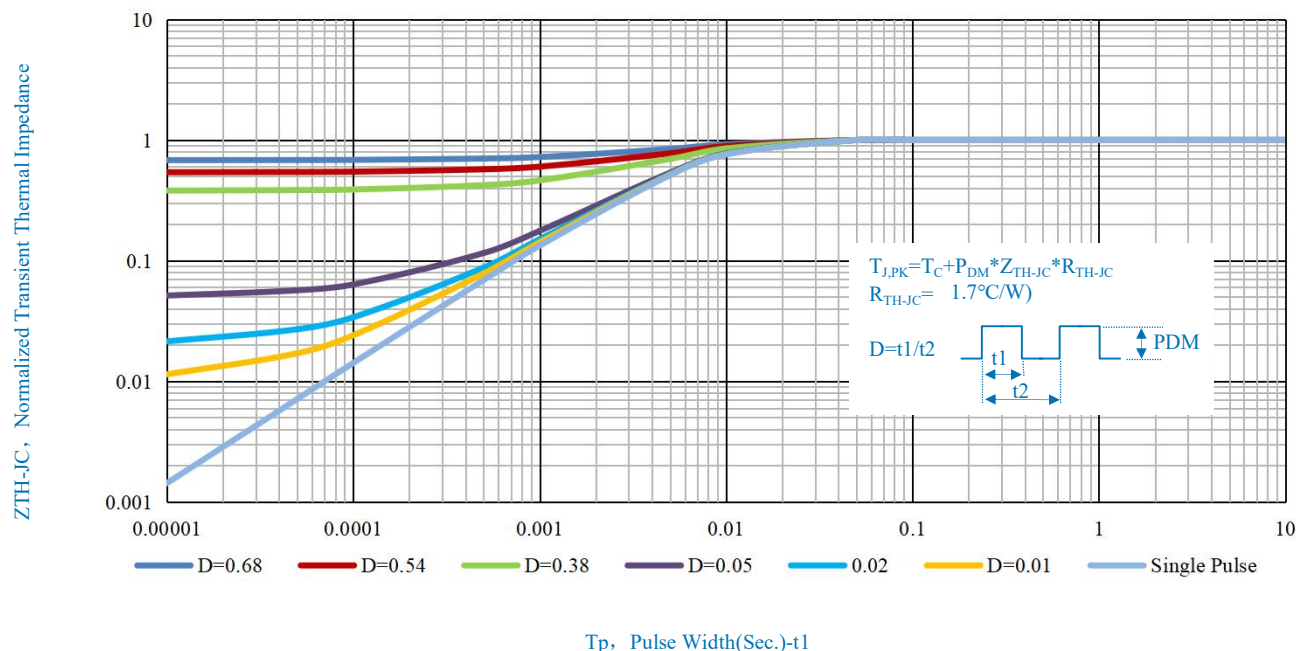


Fig.13- Normalized Maximum Transient Thermal Impedance Vs.Pulse Width

Test Circuit & Waveform

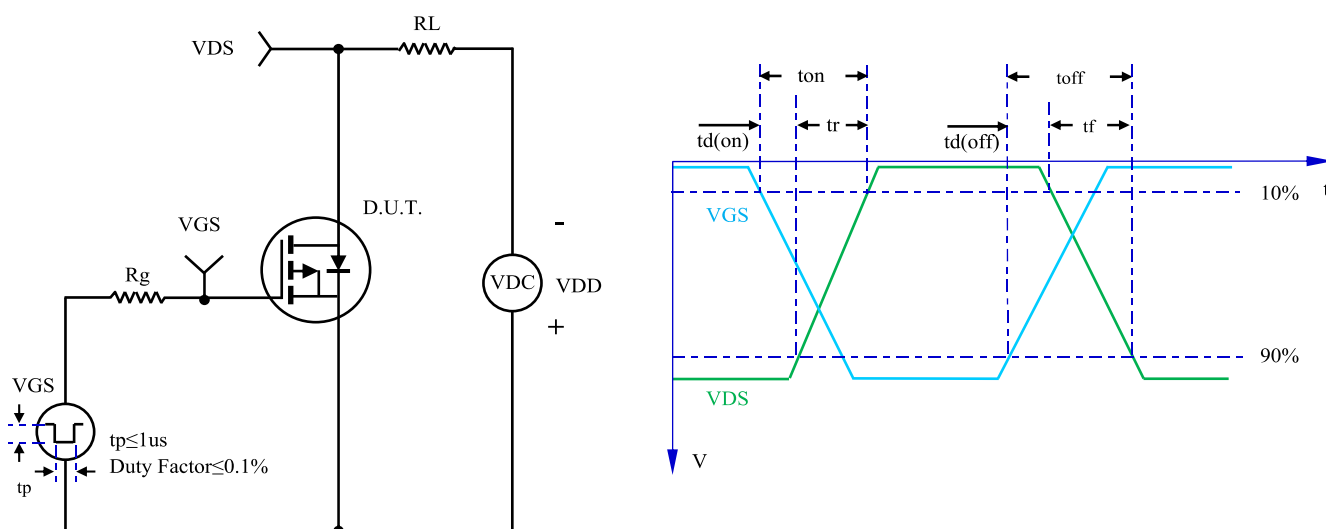


Fig.14- Resistive Switching Test Circuit & Waveform

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Test Circuit & Waveform

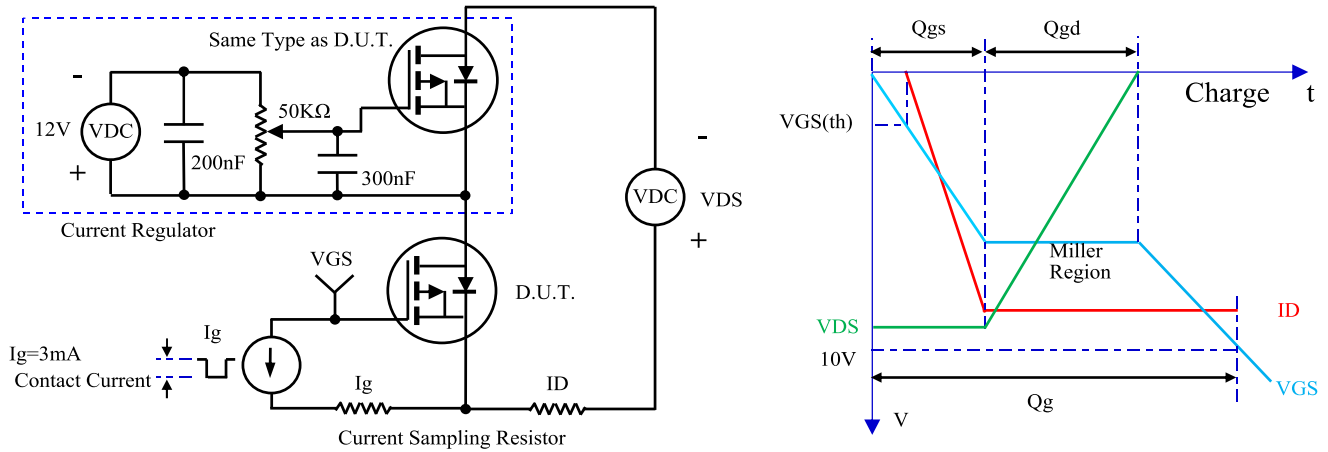


Fig.15- Gate Charge Test Circuit & Waveform

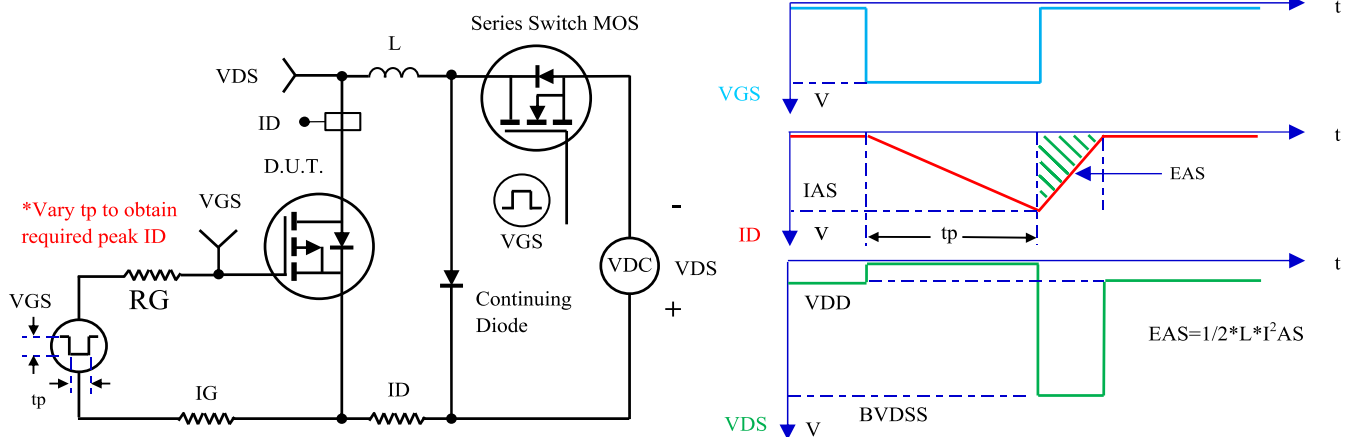


Fig.16- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

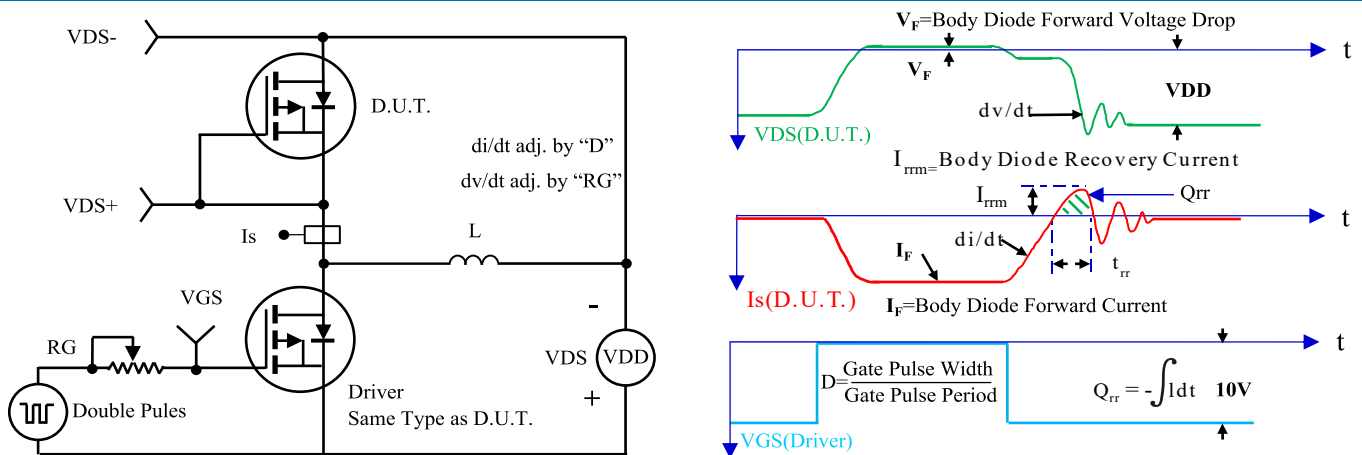


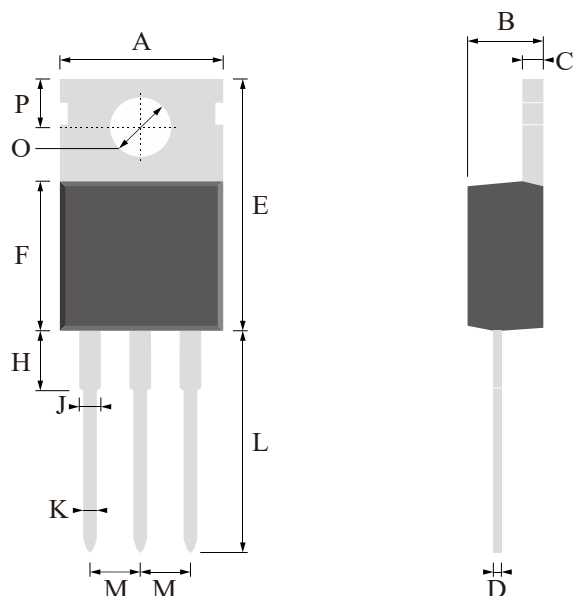
Fig.17- Diode Recovery Test Circuit & Waveform

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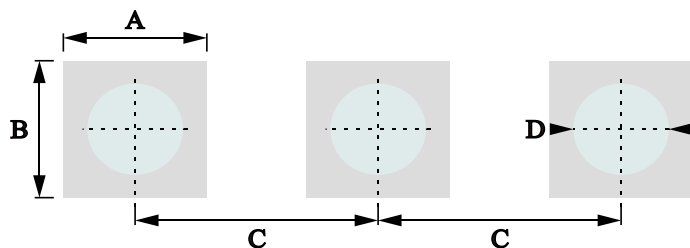
OUTLINE DRAWINGS



TO-220C

OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.25	-	10.75	0.3642	-	0.4232
B	4.15	-	4.95	0.1634	-	0.1949
C	1.10	-	1.65	0.0433	-	0.0650
D	0.25	-	0.65	0.0098	-	0.0256
E	14.50	-	16.70	0.5709	-	0.6575
F	8.40	-	9.95	0.3307	-	0.3917
L	12.15	-	14.30	0.4783	-	0.5630
H	3.00	-	3.80	0.1181	-	0.1496
J	1.05	-	1.60	0.0413	-	0.0630
K	0.65	-	0.95	0.0256	-	0.0374
M	2.10	-	2.90	0.0827	-	0.1142
O	3.20	-	4.10	0.1260	-	0.1614
P	2.45	-	3.10	0.0965	-	0.1220

RECOMMENDED LAYOUT DRAWINGS



TO-220C

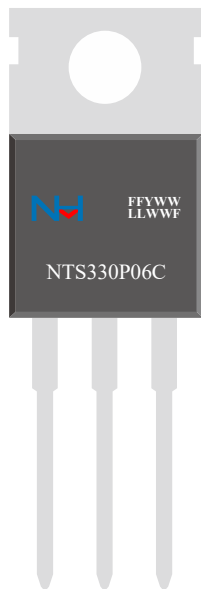
OUTLINE DIMENSIONS						
Dim.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	1.60	-	-	0.0630	-
B	-	1.60	-	-	0.0630	-
C	-	2.54	-	-	0.1000	-
D	-	1.00	-	-	0.0394	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhan Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Internal Code,According To Actual Changes
NTS330P06C=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
TO-220C	P1	2.057	Tube	50	1000	5000

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (TSmax to TP)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (TS min) -Temperature Max (TS max) -Time(ts min to ts max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (TL) - Time (tL)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(TP)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (tp)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		
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